

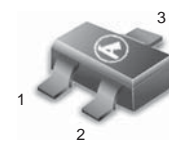
Common Cathode Silicon Dual Switching Diode

This Common Cathode Silicon Epitaxial Planar Dual Diode is designed for use in ultra high speed switching applications. This device is housed in the SC-70 package which is designed for low power surface mount applications.

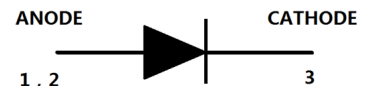
- Fast t_{rr} , < 3.0 ns
- Low C_D , < 2.0 pF
- We declare that the material of product compliance with RoHS requirements.
- S- Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable.

LM1MA141WKT1G
S-LM1MA141WKT1G
LM1MA142WKT1G
S-LM1MA142WKT1G

SC-70/SOT-323 PACKAGE
COMMON CATHODE
DUAL SWITCHING DIODE
40/80 V-100 mA
SURFACE MOUNT



SC-70



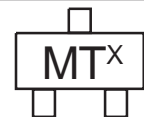
MAXIMUM RATINGS ($T_A = 25^\circ\text{C}$)

Rating		Symbol	Value	Unit
Reverse Voltage	LM1MA141WKT1G	V_R	40	V _{dc}
	LM1MA142WKT1G		80	
Peak Reverse Voltage	LM1MA141WKT1G	V_{RM}	40	V _{dc}
	LM1MA142WKT1G		80	
Forward Current	Single	I_F	100	mAdc
	Dual		150	
Peak Forward Current	Single	I_{FM}	225	mAdc
	Dual		340	
Peak Forward Surge Current	Single	$I_{FSM}^{(1)}$	500	mAdc
	Dual		750	

THERMAL CHARACTERISTICS

Rating	Symbol	Max	Unit
Power Dissipation	P_D	150	mW
Junction Temperature	T_J	150	°C
Storage Temperature	T_{stg}	-55 ~ +150	°C

Marking Symbol
 Type No. 141WK142WK
 Symbol MT MU



The "X" represents a smaller alpha digit Date Code. The Date Code indicates the actual month in which the part was manufactured.

ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$)

Characteristic		Symbol	Condition	Min	Max	Unit
Reverse Voltage Leakage Current	LM1MA141WKT1G	I_R	$V_R = 35\text{ V}$	—	0.1	μAdc
	LM1MA142WKT1G		$V_R = 75\text{ V}$	—	0.1	
Forward Voltage		V_F	$I_F = 100\text{ mA}$	—	1.2	Vdc
Reverse Breakdown Voltage	LM1MA141WKT1G	V_R	$I_R = 100\text{ }\mu\text{A}$	40	—	Vdc
	LM1MA142WKT1G			80	—	
Diode Capacitance		C_D	$V_R=0, f=1.0\text{ MHz}$	—	2.0	pF
Reverse Recovery	Time	$t_{rr}^{(2)}$	$I_F=10\text{ mA}, V_R=6.0\text{ V}$ $R_L=100\Omega, I_{rr}=0.1 I_R$	—	3.0	ns

1. $t = 1\text{ SEC}$

2. t_{rr} Test Circuit

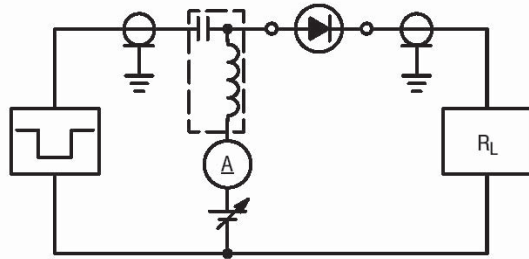
**LM1MA141WKT1G, S-LM1MA141WKT1G
LM1MA142WKT1G, S-LM1MA142WKT1G**

DEVICE MARKING AND ORDERING INFORMATION

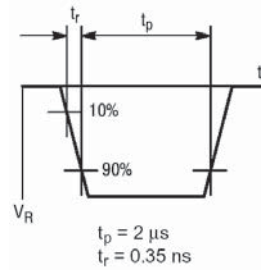
Device	Marking	Package	Shipping
LM1MA141WKT1G S-LM1MA141WKT1G	MT	SOT-323/SC-70	3000/Tape&Reel
LM1MA141WKT3G S-LM1MA141WKT3G	MT	SOT-323/SC-70	10000/Tape&Reel
LM1MA142WKT1G S-LM1MA142WKT1G	MU	SOT-323/SC-70	3000/Tape&Reel
LM1MA142WKT3G S-LM1MA142WKT3G	MU	SOT-323/SC-70	10000/Tape&Reel

LM1MA141WKT1G, S-LM1MA141WKT1G
LM1MA142WKT1G, S-LM1MA142WKT1G

RECOVERY TIME EQUIVALENT TEST CIRCUIT



INPUT PULSE



OUTPUT PULSE

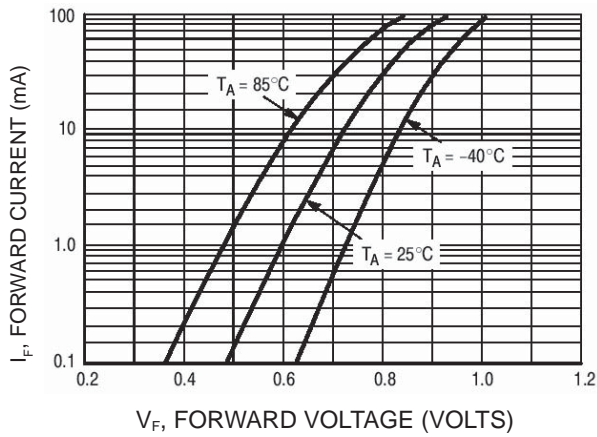
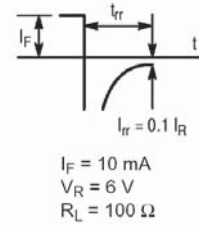


Figure 1. Forward Voltage

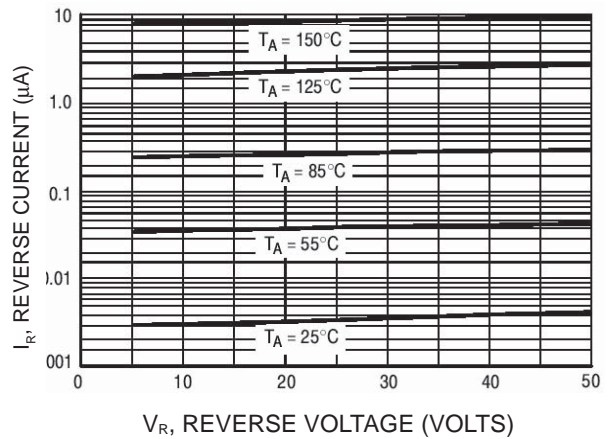


Figure 2. Reverse Current

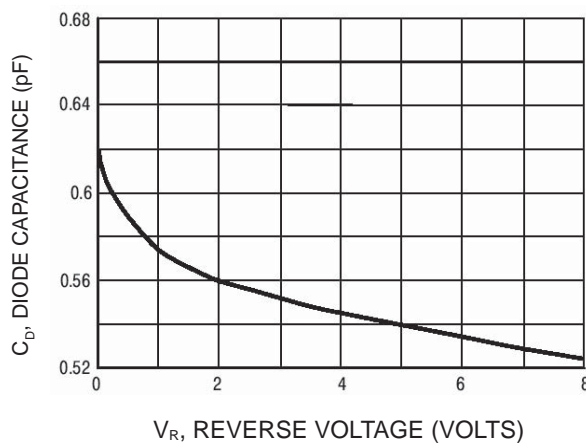
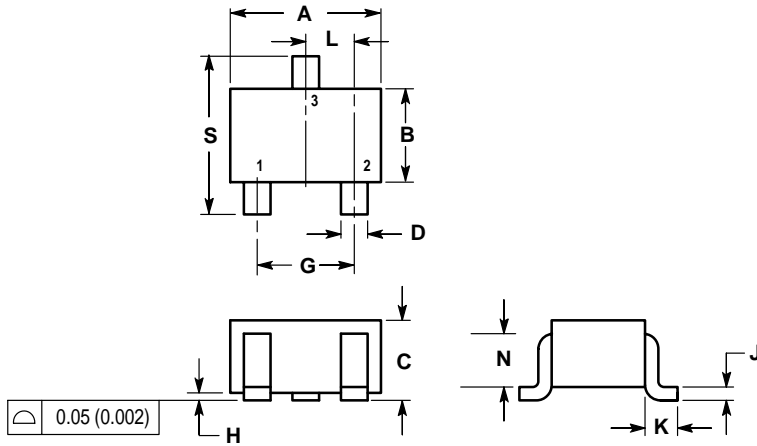


Figure 3. Diode Capacitance

**LM1MA141WKT1G, S-LM1MA141WKT1G
LM1MA142WKT1G, S-LM1MA142WKT1G**
SC-70
NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.



DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.071	0.087	1.80	2.20
B	0.045	0.053	1.15	1.35
C	0.032	0.040	0.80	1.00
D	0.012	0.016	0.30	0.40
G	0.047	0.055	1.20	1.40
H	0.000	0.004	0.00	0.10
J	0.004	0.010	0.10	0.25
K	0.017 REF		0.425 REF	
L	0.026 BSC		0.650 BSC	
N	0.028 REF		0.700 REF	
S	0.079	0.095	2.00	2.40

